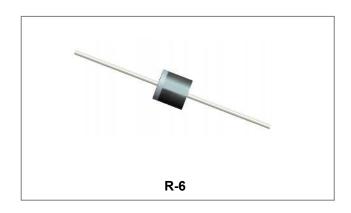






ST1545AX SCHOTTKY BARRIER RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	45	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C = 75°C, rectangular wave form	15	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C = 25°C	200	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*		@ 5A, Pulse, T _J = 25 °C	0.38	_	
	V _{F1}	@ 7.5A, Pulse, T _J = 25 °C	0.40	-	V
		@ 15A, Pulse, T _J = 25 °C	0.46	0.59	
		@ 5A, Pulse, T _J = 125 °C	0.25	-	
	V _{F2}	@ 7.5A, Pulse, T _J = 125 °C	0.28	_	V
		@ 15A, Pulse, T _J = 125 °C	0.37	0.54	
Reverse Current*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.2	0.8	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	110	150	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	868	-	pF

^{*} Pulse width < 300 μ s, duty cycle < 2%

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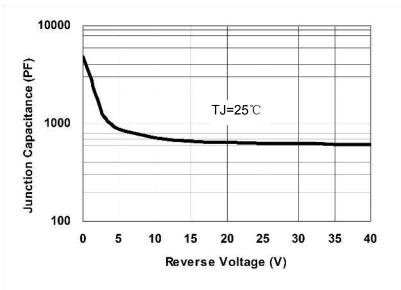




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification Unit	
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	DC operation	55	°C/W
Approximate Weight	wt	-	2.24	g
Case Style	R-6			

Ratings and Characteristics Curves



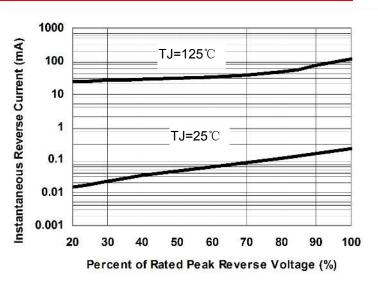


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

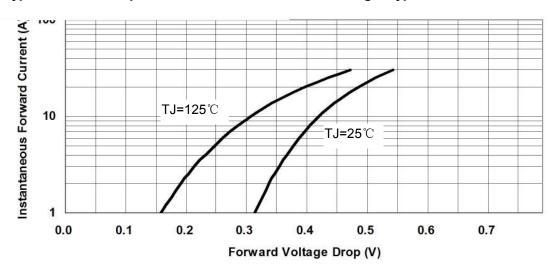


Fig.3-Typical Instantaneous Forward Voltage Characteristics

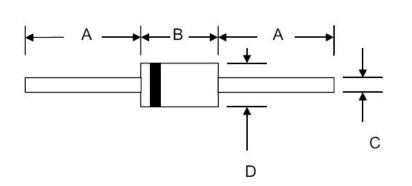
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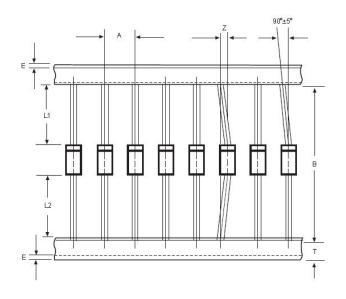


Mechanical Dimensions R-6



CYMPOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
Α	25.4	-	1.000	-	
В	8.60	9.10	0.340	0.360	
С	1.2	1.3	0.048	0.052	
D	8.60	9.10	0.340	0.360	

Carrier Tape Specification R-6



SYMBOL	Millimeters		
	Min.	Max.	
А	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	

Ordering Information

Device	Package	Shipping
ST1545AX	R-6(Pb-Free)	500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

S = Device Type
T = Ultralow VF
15 = Forward Current (15A)
45 = Reverse Voltage (45V)
AX = Package type
SSG = SSG
YY = Year

= Week = Lot Number

Cautions: Molding resin

 $\mathsf{W}\mathsf{W}$

Epoxy resin UL:94V-0

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